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In a semiconductor laser device, an AlGaIn buffer layer, a GaN layer, an n-GaN layer, an n-AlGaIn cladding layer, an MQW light emitting layer, a p-AlGaIn cladding layer, a p-first GaN cap layer, a current blocking layer composed of n-AlGaIn, and a p-second GaN cap layer are stacked in this order on a sapphire substrate, and a ridge portion having an upper surface having a width W_1 is formed by etching. The current blocking layer has an opening having a width W_2 on the upper surface of the ridge portion. The width W_2 of the opening is smaller than the width W_1 of the upper surface of the ridge portion. Accordingly, in a light emitting region of the MQW light emitting layer, a saturable light absorbing region is formed on both sides of a current injection region.